

# SSM3K347R

## 1. Applications

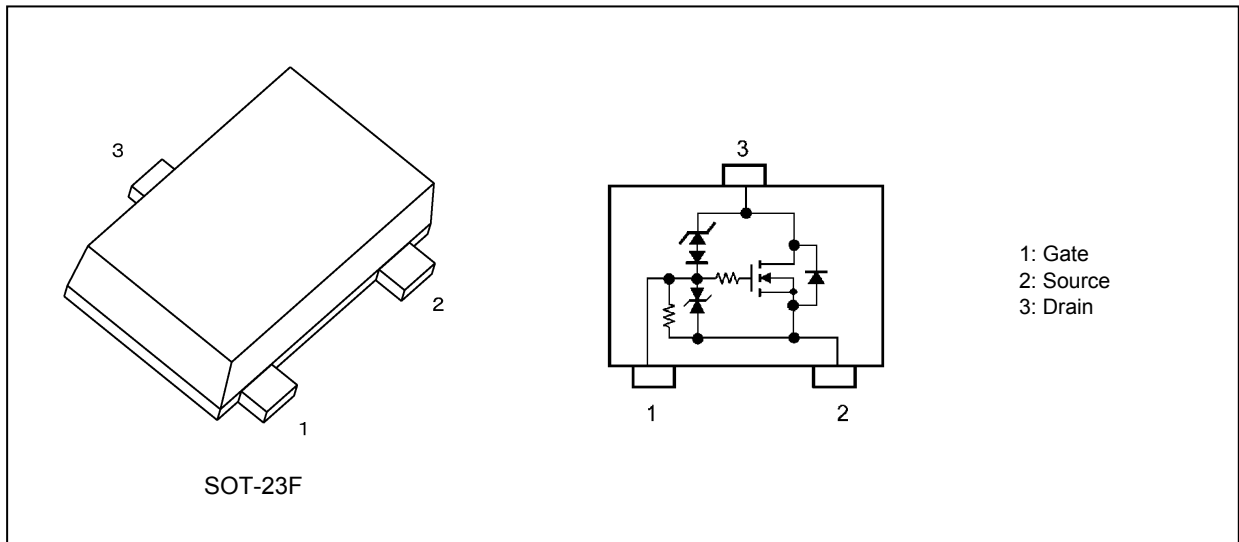
- Relay Drivers

## 2. Features

- (1) AEC-Q101 (Rev. D) qualified. (Note 1)
- (2) 4.0 V drive
- (3) Built-in pull down resistance 47 kΩ.
- (4) Low drain-source on-resistance  
 :  $R_{DS(ON)} = 480 \text{ m}\Omega$  (max) (@ $V_{GS} = 4.0 \text{ V}$ )  
 $R_{DS(ON)} = 410 \text{ m}\Omega$  (max) (@ $V_{GS} = 4.5 \text{ V}$ )  
 $R_{DS(ON)} = 340 \text{ m}\Omega$  (max) (@ $V_{GS} = 10 \text{ V}$ )

Note 1: For detail information, please contact to our sales.

## 3. Packaging and Pin Assignment



Start of commercial production

2016-04

**4. Absolute Maximum Ratings (Note) (Unless otherwise specified,  $T_a = 25\text{ }^\circ\text{C}$ )**

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DS(DC)}$	38	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	
Drain current (DC) (Note 1)	$I_D$	2	A
Drain current (pulsed) (Note 1), (Note 2)	$I_{DP}$	4	
Power dissipation (Note 3)	$P_D$	1	W
Power dissipation (t = 10 s) (Note 3)	$P_D$	2	
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Single-pulse active clamp capability (Note 4)	$E_{AS}$	2.2	mJ
Storage temperature	$T_{stg}$	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed  $150\text{ }^\circ\text{C}$ .

Note 2: pulse width  $\leq 10\text{ }\mu\text{s}$ , Duty  $\leq 1\%$

Note 3: Device mounted on a  $25.4\text{ mm} \times 25.4\text{ mm} \times 1.6\text{ mm}$  FR4 glass epoxy board (Cu pad:  $645\text{ mm}^2$ )

Note 4:  $V_{DD} = 25\text{ V}$ ,  $T_{ch} = 25\text{ }^\circ\text{C}$  (Initial state)

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance,  $R_{th(ch-a)}$ , and the drain power dissipation,  $P_D$ , vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

**5. Electrical Characteristics**

**5.1. Static Characteristics (Unless otherwise specified,  $T_a = 25\text{ }^\circ\text{C}$ )**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain-source clamp voltage	$V_{(CL)DSS}$	$I_D = 1\text{ mA}, V_{GS} = 0\text{ V}$	38	43	48	V
Drain cut-off current	$I_{DSS}$	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	$\mu\text{A}$
Gate leakage current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$	—	—	$\pm 152$	
Gate threshold voltage (Note 1)	$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.4	—	2.4	V
Forward transfer admittance (Note 2)	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 1.0\text{ A}$	—	4.1	—	S
Drain-source on-resistance (Note 2)	$R_{DS(ON)}$	$I_D = 0.5\text{ A}, V_{GS} = 4.0\text{ V}$	—	350	480	$\text{m}\Omega$
		$I_D = 1.0\text{ A}, V_{GS} = 4.5\text{ V}$	—	340	410	
		$I_D = 1.0\text{ A}, V_{GS} = 10\text{ V}$	—	280	340	
Pull-down resistance	$R_{pd}$	—	32.9	47	61.1	$\text{k}\Omega$

Note 1: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to be below (0.1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ .

Take this into consideration when using the device.

Note 2: Pulse measurement.

**5.2. Dynamic Characteristics (Unless otherwise specified,  $T_a = 25\text{ }^\circ\text{C}$ )**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	86	—	$\mu\text{F}$
Reverse transfer capacitance	$C_{rss}$		—	13	—	
Output capacitance	$C_{oss}$		—	27	—	
Switching time (turn-on time)	$t_{on}$	$V_{DD} = 20\text{ V}, I_D = 0.5\text{ A}, V_{GS} = 0\text{ to }4.5\text{ V}, R_G = 50\text{ }\Omega$ Duty $\leq 1\%$ , Input: $t_r, t_f < 5\text{ ns}$ , Common source, See Chapter 5.3.	—	380	—	ns
Switching time (turn-off time)	$t_{off}$		—	800	—	

**5.3. Switching Time Test Circuit**

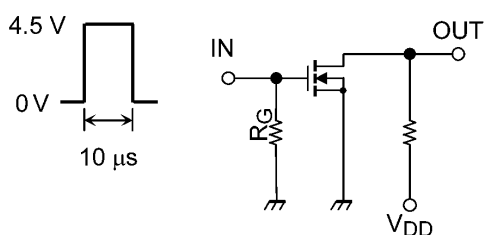


Fig. 5.3.1 Switching Time Test Circuit

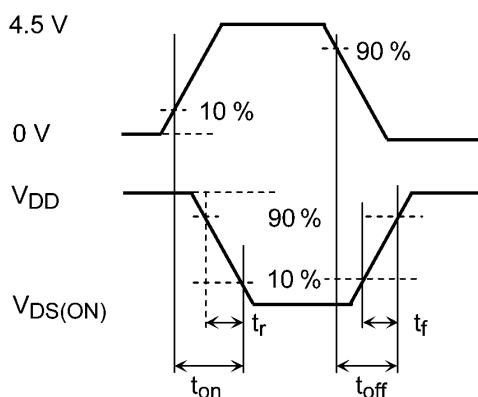


Fig. 5.3.2 Input Waveform/Output Waveform

**5.4. Gate Charge Characteristics (Unless otherwise specified,  $T_a = 25\text{ }^\circ\text{C}$ )**

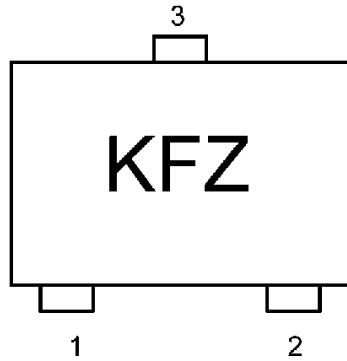
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} = 20\text{ V}, I_D = 1.0\text{ A}, V_{GS} = 10\text{ V}$	—	2.5	—	nC
Gate-source charge 1	$Q_{gs1}$		—	0.8	—	
Gate-drain charge	$Q_{gd}$		—	0.5	—	

**5.5. Source-Drain Characteristics (Unless otherwise specified,  $T_a = 25\text{ }^\circ\text{C}$ )**

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage (Note 1)	$V_{DSF}$	$I_D = -2\text{ A}, V_{GS} = 0\text{ V}$	—	-0.87	-1.2	V

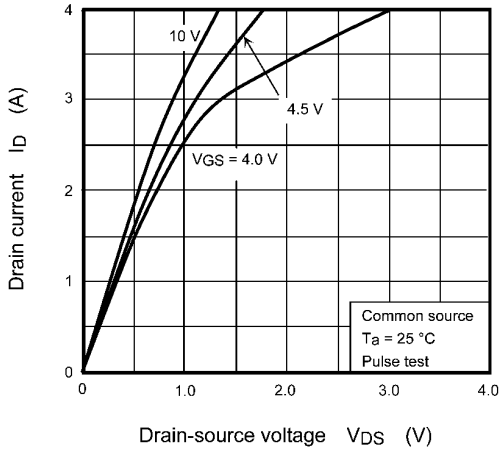
Note 1: Pulse measurement.

**6. Marking**

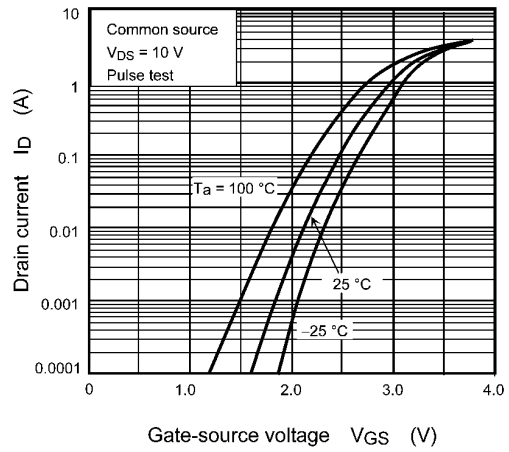


**Fig. 6.1 Marking**

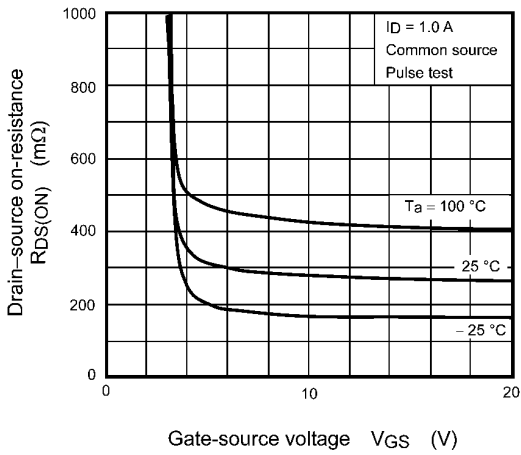
**7. Characteristics Curves (Note)**



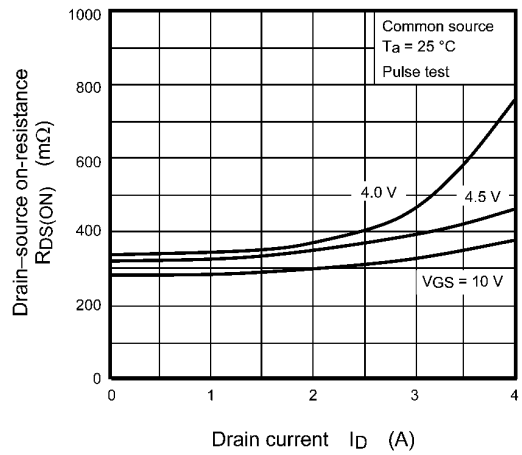
**Fig. 7.1  $I_D - V_{DS}$**



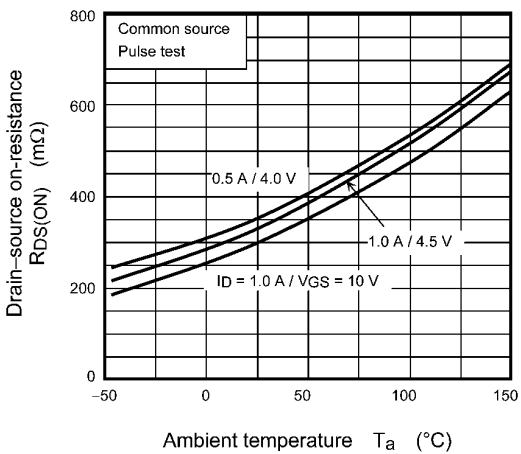
**Fig. 7.2  $I_D - V_{GS}$**



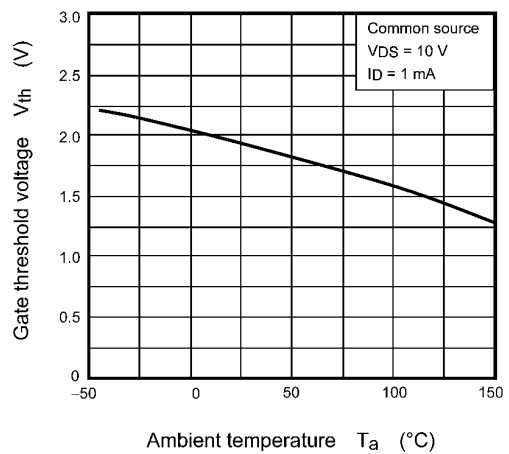
**Fig. 7.3  $R_{DS(ON)} - V_{GS}$**



**Fig. 7.4  $R_{DS(ON)} - I_D$**



**Fig. 7.5  $R_{DS(ON)} - T_a$**



**Fig. 7.6  $V_{th} - T_a$**

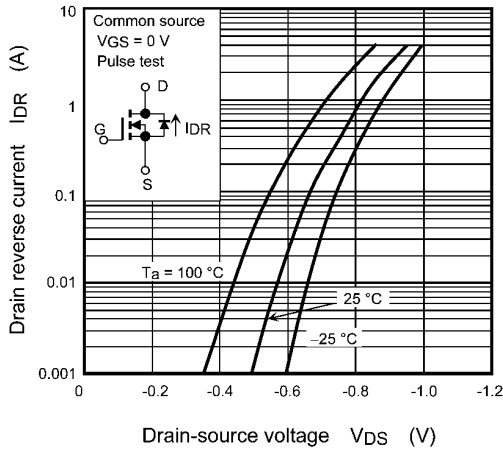


Fig. 7.7  $I_{DR} - V_{DS}$

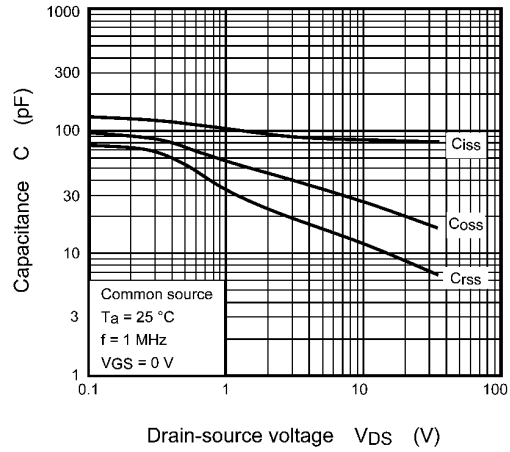


Fig. 7.8  $C - V_{DS}$

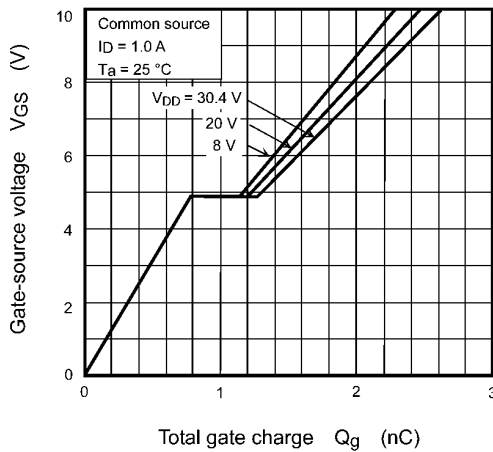


Fig. 7.9 Dynamic Input Characteristics

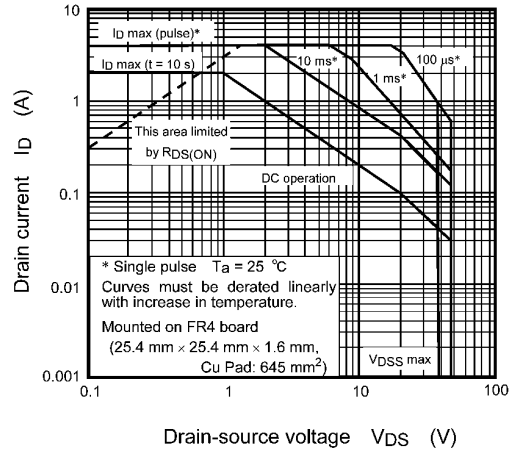


Fig. 7.10 Safe Operating Area

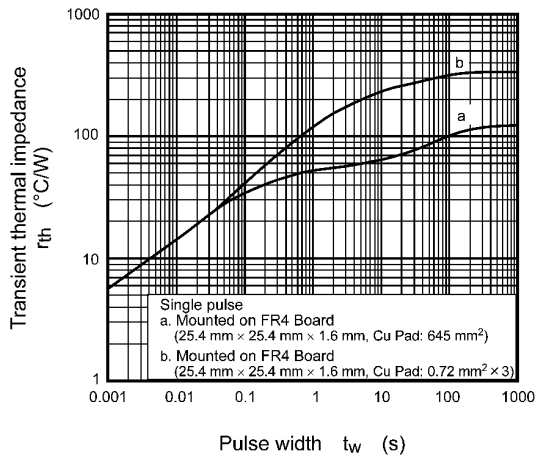


Fig. 7.11  $r_{th} - t_w$

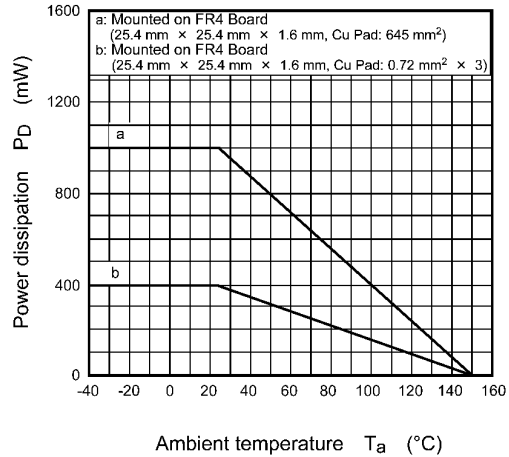
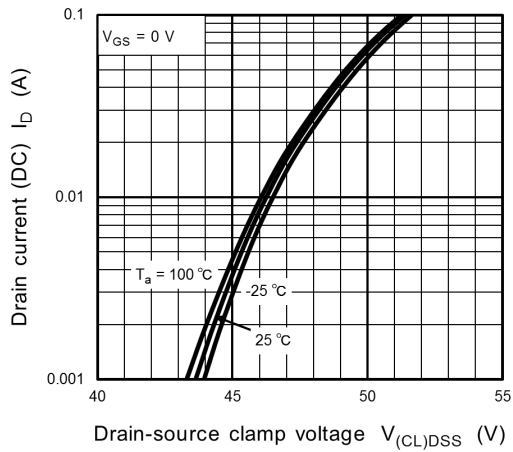


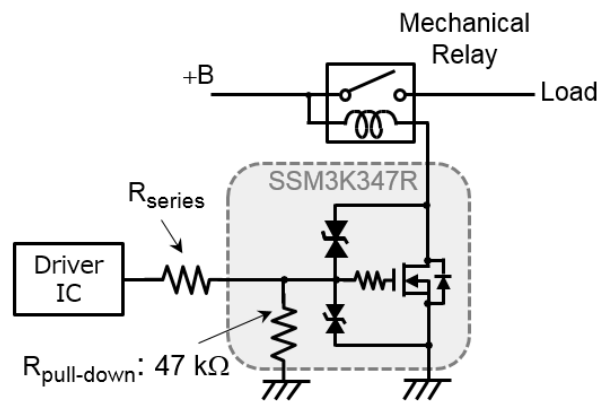
Fig. 7.12  $P_D - T_a$



**Fig. 7.13**  $I_D - V_{(CL)DSS}$

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

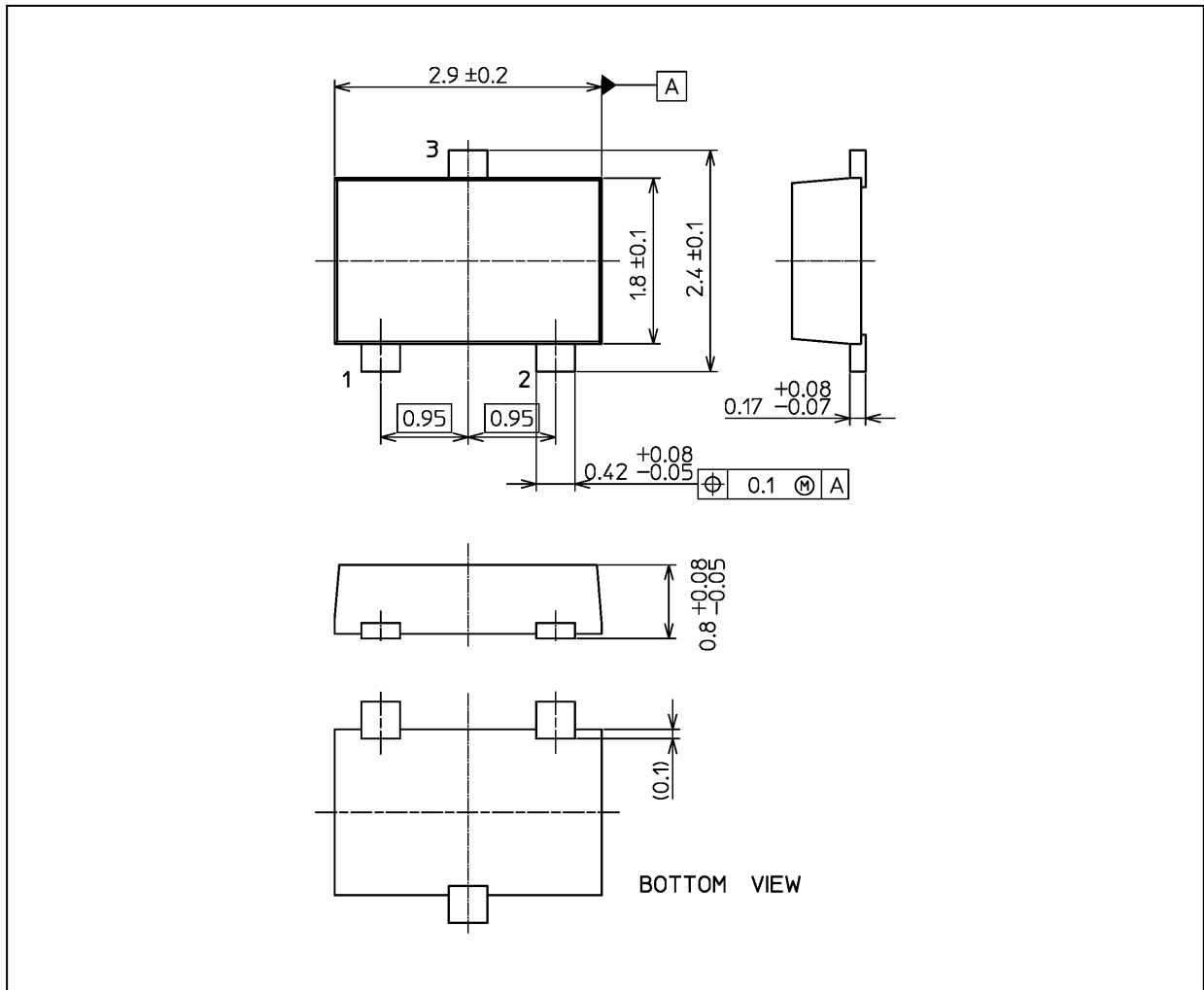
**8. ACTIVE CLAMP APPLICATION**



$R_{series}$ : Input series resistance is necessary to set to a value (range: 1 k $\Omega$  to 5 k $\Omega$ )

Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

Package Name(s)
Nickname: SOT-23F



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